MLSQ4616A

30V N-Channel and P-Channel MOSFET

Features

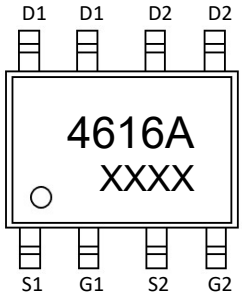
- Trench Power LV MOSFET technology
- High density cell design for Low $R_{DS(ON)}$
- High Speed switching

Application

- Battery protection
- Power management
- Load switch

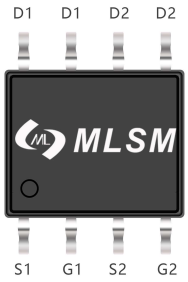
Product Summary

V_{DS}	$R_{DS(ON)}$ MAX	I_D MAX
30V	20mΩ@10V	8A
	28mΩ@4.5V	
-30V	28mΩ@-10V	-7A
	40mΩ@-4.5V	

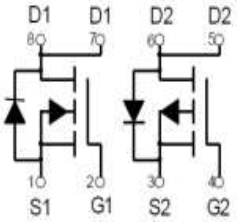


4616A : Device code
XXXX : Code

Marking and pin assignment



SOP-8 top view



Schematic diagram

Pb-Free RoHS Halogen-Free

Absolute Maximum Ratings (TA=25℃unless otherwise noted)					
Symbol	**Parameter**		**N-Channel**	**P-Channel**	**Unit**
Common Ratings (TC=25°C Unless Otherwise Noted)					
V_{DS}	Drain-Source Breakdown Voltage		30	-30	V
V_{GS}	Gate-Source Voltage		±20	±20	V
T_J	Maximum Junction Temperature		150	150	°C
T_{STG}	Storage Temperature Range		-55 to 150	-55 to 150	°C
I_S	Diode Continuous Forward Current	Tc=25°C	8	-7	A
Mounted on Large Heat Sink					
I_{DM}	Pulse Drain Current Tested	Tc=25°C	40	-40	A
I_D	Continuous Drain Current	Tc=25°C	8	-7	A
P_D	Maximum Power Dissipation	Tc=25°C	2	2	W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient		62.5	62.5	°C/W

Ordering Information (Example)						
Type	**Package**	**Marking**	**Minimum Package(pcs)**	**Inner Box Quantity(pcs)**	**Outer Carton Quantity(pcs)**	**Delivery Mode**
MLSQ4616A	SOP-8	4616A	3,000	6,000	42,000	13"reel

N-Ch Electrical Characteristics (TJ=25℃ unless otherwise noted)						
Symbol	**Parameter**	**Condition**	**Min**	**Typ**	**Max**	**Unit**
Static Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
$BV_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250μA	30	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=30V, V_{GS}=0V	--	--	1	μA
I_{GSS}	Gate-Body Leakage Current	V_{GS}=±20V, V_{DS}=0V	--	--	±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250μA	1.2	1.8	2.4	V
$R_{DS(on)}$	Drain-Source On-State Resistance	V_{GS}=10V, I_D=8A	--	16.5	20	mΩ
		V_{GS}=4.5V, I_D=6A	--	19.5	28	mΩ
Dynamic Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
C_{ISS}	Input Capacitance	V_{DS}=15V, V_{GS}=0V, f=1MHz	--	740	--	pF
C_{OSS}	Output Capacitance		--	110	--	pF
C_{RSS}	Reverse Transfer Capacitance		--	82	--	pF
Switching Characteristics						
Qg	Total Gate Charge	V_{DS}=15V, I_D=8A, V_{GS}=10V	--	15	--	nC
Qgs	Gate Source Charge		--	2.5	--	nC
Qgd	Gate Drain Charge		--	3	--	nC
td(on)	Turn-on Delay Time	V_{DS}=15V, R_L=1.8Ω, V_{GS}=10V, R_G=3Ω	--	5	--	nS
tr	Turn-on Rise Time		--	3.5	--	nS
td(off)	Turn-Off Delay Time		--	19	--	nS
tf	Turn-Off Fall Time		--	3.5	--	nS
Source- Drain Diode Characteristics						
V_{SD}	Forward on voltage	Tj=25℃, Is=8A	--	--	1.2	V

P-Ch Electrical Characteristics (TJ=25℃ unless otherwise noted)						
Symbol	**Parameter**	**Condition**	**Min**	**Typ**	**Max**	**Unit**
Static Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
$BV_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=-250μA	-30	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=-30V, V_{GS}=0V	--	--	-1	μA
I_{GSS}	Gate-Body Leakage Current	V_{GS}=±20V, V_{DS}=0V	--	--	±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=-250μA	-1.4	-2.0	-2.5	V
$R_{DS(on)}$	Drain-Source On-State Resistance	V_{GS}=-10V, I_D=-7.0A	--	23	28	mΩ
		V_{GS}=-4.5V, I_D=-3.5A	--	32	40	mΩ
Dynamic Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
C_{ISS}	Input Capacitance	V_{DS}=-15V, V_{GS}=0V, f=1MHz	--	1040	--	pF
C_{OSS}	Output Capacitance		--	179	--	pF
C_{RSS}	Reverse Transfer Capacitance		--	134	--	pF
Switching Characteristics						
Q_g	Total Gate Charge	V_{DS}=-15V, I_D=-7A, V_{GS}=-10V	--	19	--	nC
Q_{gs}	Gate Source Charge		--	3.6	--	nC
Q_{gd}	Gate Drain Charge		--	4.6	--	nC
$t_{d(on)}$	Turn-on Delay Time	V_{DD}=-15V, I_D=-7A, V_{GS}=-10V, R_G=3Ω	--	10	--	nS
t_r	Turn-on Rise Time		--	5.5	--	nS
$t_{d(off)}$	Turn-Off Delay Time		--	26	--	nS
t_f	Turn-Off Fall Time		--	9	--	nS
Source- Drain Diode Characteristics						
V_{SD}	Forward on voltage	Tj=25℃, Is=-7A	--	--	-1.2	V

N-Channel Typical Operating Characteristics

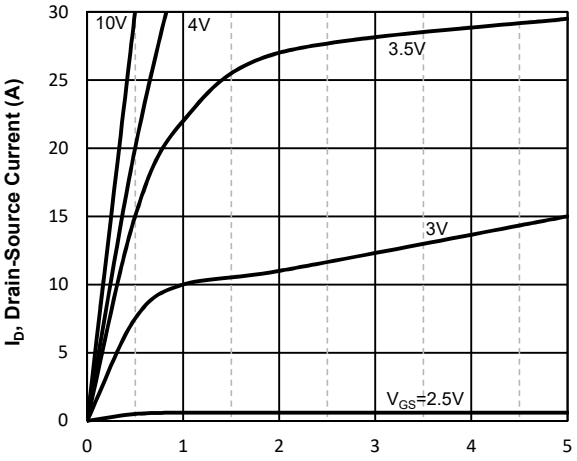


Fig1. Typical Output Characteristics

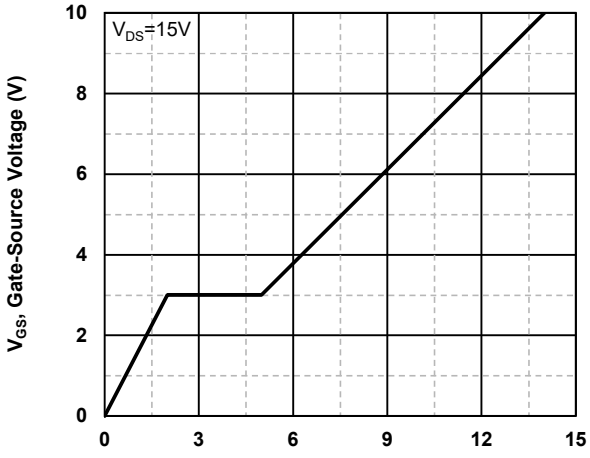


Fig2. Typical Gate Charge Vs.Gate-Source Voltage

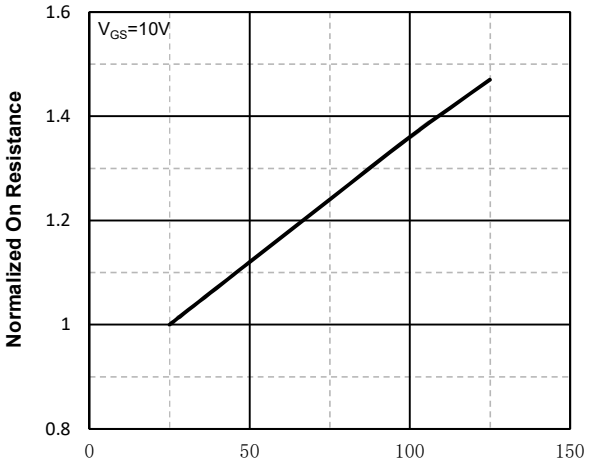


Fig3. Normalized On-Resistance Vs. Temperature

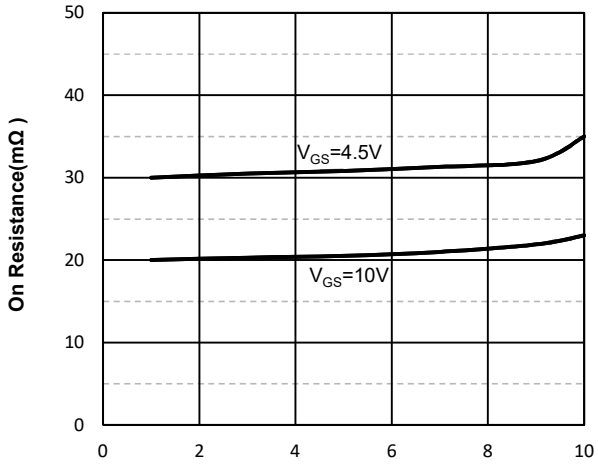


Fig4. On-Resistance Vs. Drain-Source Current

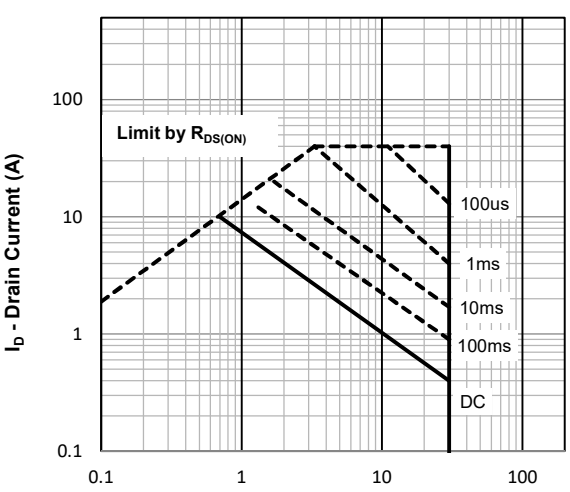


Fig5. Maximum Safe Operating Area

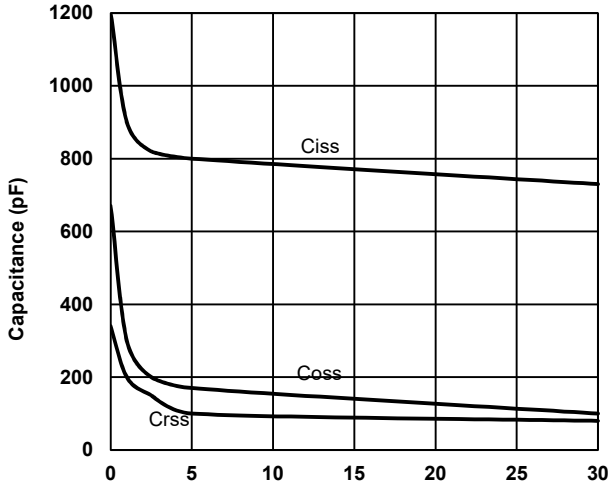


Fig6 Typical Capacitance Vs.Drain-Source Voltage

P-Channel Typical Operating Characteristics

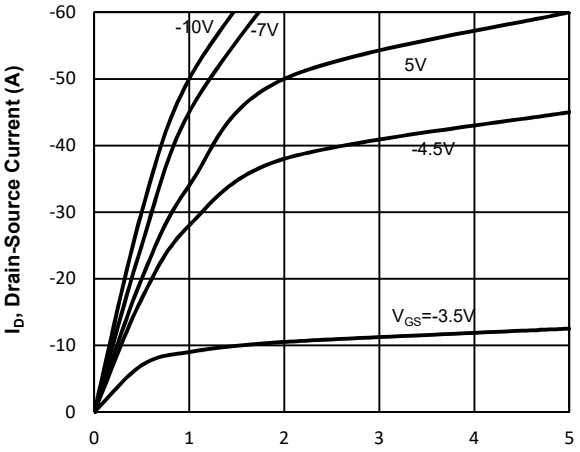


Fig7. Typical Output Characteristics

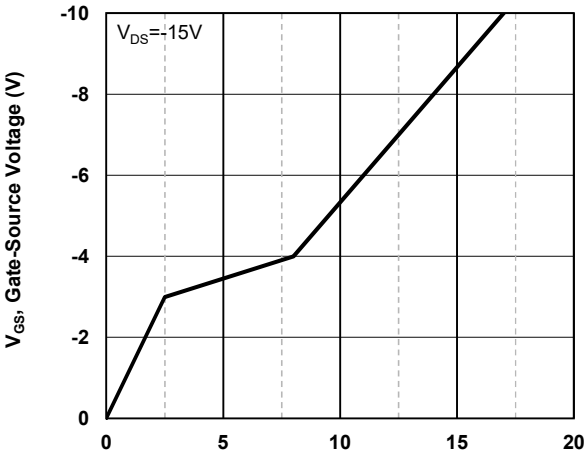


Fig8. Typical Gate Charge Vs.Gate-Source Voltage

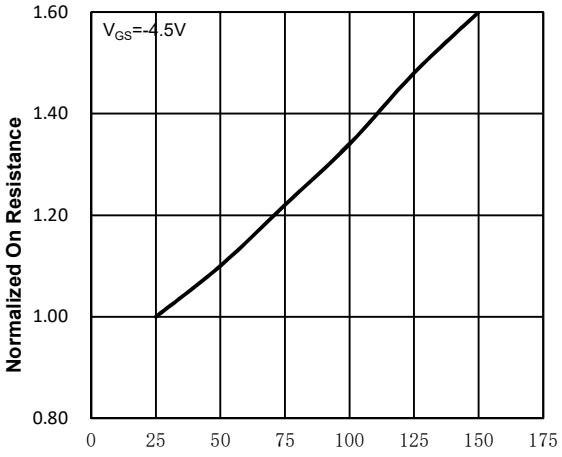


Fig9. Normalized On-Resistance Vs. Temperature

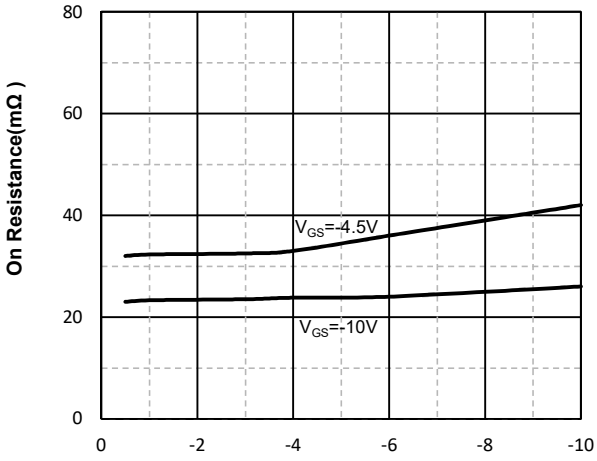


Fig10. On-Resistance Vs. Drain-Source Current

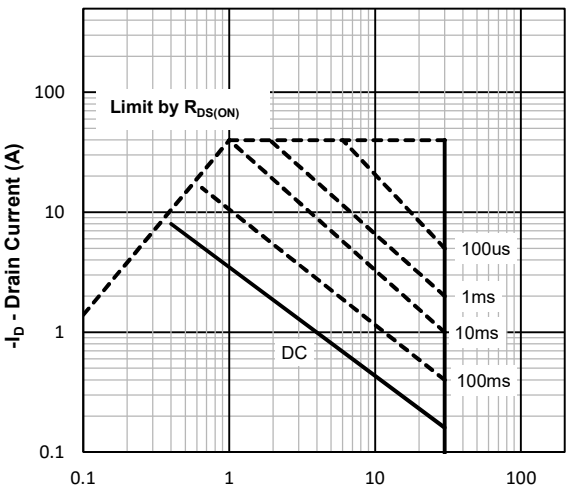


Fig11. Maximum Safe Operating Area

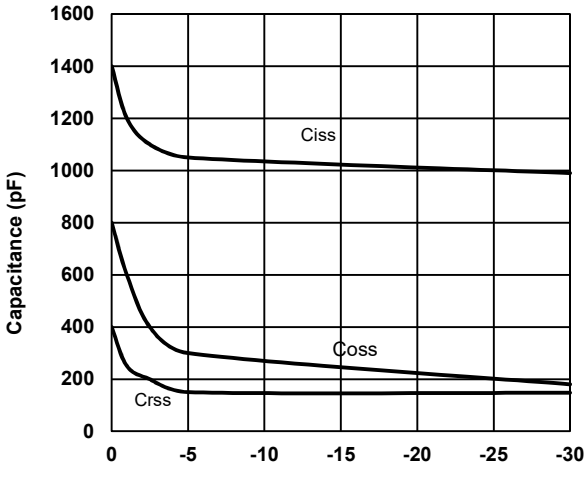
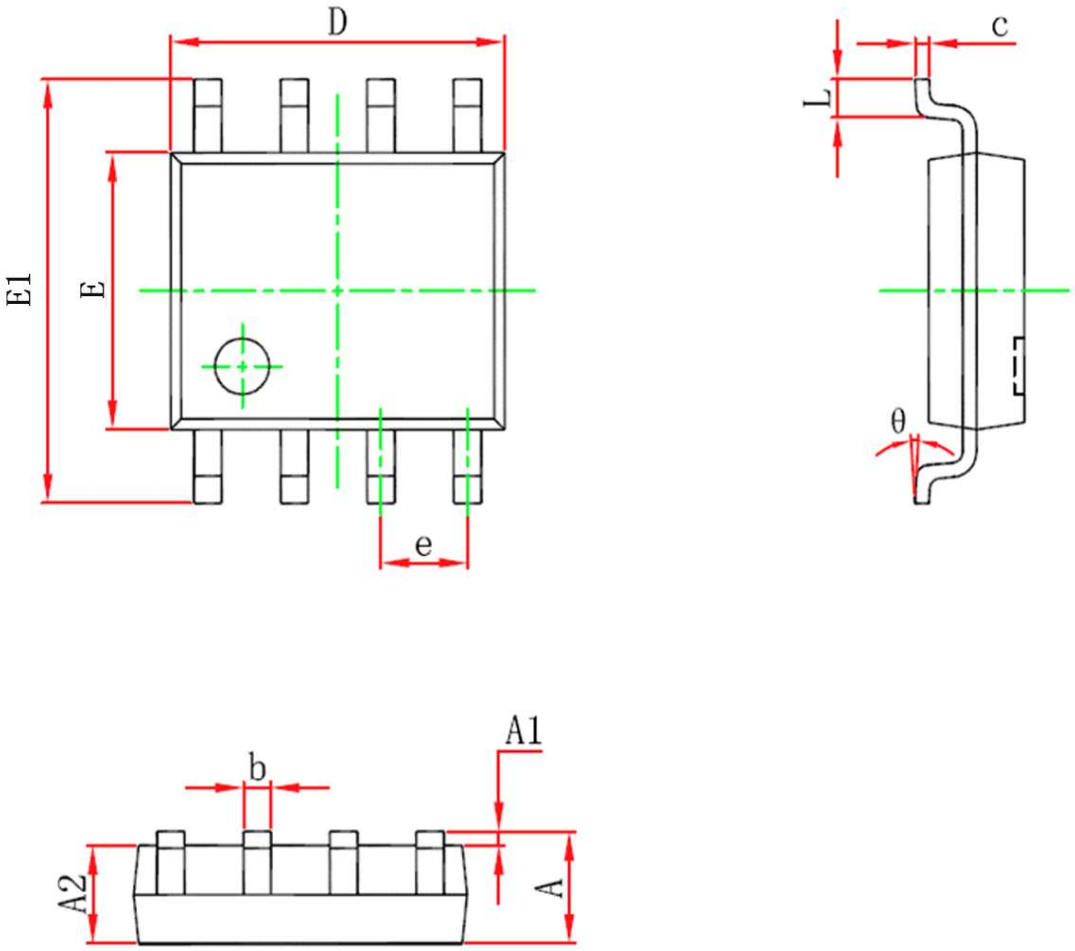


Fig12 Typical Capacitance Vs.Drain-Source Voltage

SOP-8 Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	1.450	1.750	0.057	0.068
A1	0.100	0.250	0.003	0.009
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.012	0.020
c	0.170	0.250	0.006	0.009
D	4.700	5.100	0.185	0.200
e	1.270(BSC)		0.050(BSC)	
E	3.800	4.000	0.149	0.157
E1	5.800	6.200	0.228	0.244
L	0.400	1.270	0.015	0.050
θ	0°	8°	0°	8°